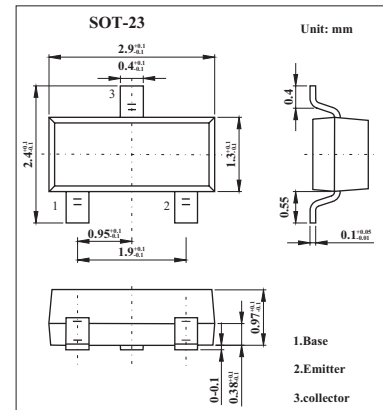


## Silicon RF Switching Diode

**BAT18;BAT18-04**  
**BAT18-05;BAT18-06**
**■ Features**

- Low-loss VHF/UHF switch above 10 MHz
- Pin diode with low forward resistance


**■ Absolute Maximum Ratings**  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Forward Current	$I_F$	100	mA
Operating and storage temperature range	$T_{op}, T_{stg}$	-55 to +150	$^\circ\text{C}$
Junction - ambient	$R_{th JA}$	$\leq 450$	K/W

**■ Electrical Characteristics**  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 100 \text{ mA}$		0.38	1.2	V
Reverse current	$I_R$	$V_R = 20 \text{ V}$			20	nA
		$V_R = 20 \text{ V}, T_A = 60^\circ\text{C}$			200	
Diode capacitance	$C_T$	$V_R = 20 \text{ V}, f = 1 \text{ MHz}$		0.75	1	pF
Forward resistance	$r_f$	$I_F = 5 \text{ mA}, f = 100 \text{ MHz}$		0.4	0.7	$\Omega$
Series inductance	$L_s$			2		nH

**■ Marking**

Type	BAT18	BAT18-04	BAT18-05	BAT18-06
Marking	A2	AU	AS	AT